

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	Package	I_D $T_A = +25^\circ C$
20V	11mΩ @ $V_{GS} = 4.5V$	U-DFN2020-6	10.5A
	13mΩ @ $V_{GS} = 2.5V$	U-DFN2020-6	9.4A
	30mΩ @ $V_{GS} = 1.8V$	U-DFN2020-6	6.5A
	50mΩ @ $V_{GS} = 1.5V$	U-DFN2020-6	5.5A

Description

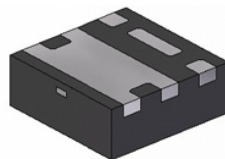
This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

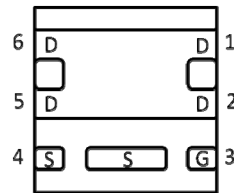
- General Purpose Interfacing Switch
- Power Management Functions



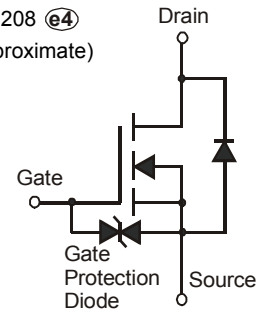
U-DFN2020-6



Bottom View



Pin Out



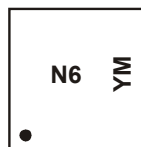
Equivalent Circuit

Ordering Information (Note 5)

Part Number	Compliance	Case	Quantity per reel
DMN2013UFDE-7	Standard	U-DFN2020-6	3,000
DMN2013UFDEQ-7	Automotive	U-DFN2020-6	3,000
DMN2013UFDE-13	Standard	U-DFN2020-6	10,000
DMN2013UFDEQ-13	Automotive	U-DFN2020-6	10,000

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



N6 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: Y = 2011)
M = Month (ex: 9 = September)

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 7) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	10.5 8.5	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	12.5 10.0	A
Continuous Drain Current (Note 7) V _{GS} = 2.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	9.4 7.5	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	11.2 8.8	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	80	A
Maximum Body Diode Continuous Current			I _S	2.5	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	0.66	W
	T _A = +70°C		0.42	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	189	°C/W
	t < 10s		132	
Total Power Dissipation (Note 7)	T _A = +25°C	P _D	2.03	W
	T _A = +70°C		1.31	
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	R _{θJA}	61	°C/W
	t < 10s		43	
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	9.3	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±2	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	0.5	—	1.1	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	8.4	11	mΩ	V _{GS} = 4.5V, I _D = 8.5A
			9.8	13		V _{GS} = 2.5V, I _D = 8.5A
			12	30		V _{GS} = 1.8V, I _D = 1A
			15	50		V _{GS} = 1.5V, I _D = 0.5A
Forward Transfer Admittance	Y _{fs}	—	10	—	S	V _{DS} = 5V, I _D = 4A
Diode Forward Voltage	V _{SD}	—	—	1.2	V	V _{GS} = 0V, I _S = 8.5A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	2453	—	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	275	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	257	—	pF	
Gate Resistance	R _g	—	1.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	14.3	—	nC	V _{DS} = 10V, I _D = 8.5A
Total Gate Charge (V _{GS} = 8V)	Q _g	—	25.8	—	nC	
Gate-Source Charge	Q _{gs}	—	1.8	—	nC	
Gate-Drain Charge	Q _{gd}	—	2.1	—	nC	
Turn-On Delay Time	t _{D(on)}	—	9.9	—	ns	V _{DS} = 10V, I _D = 8.5A V _{GS} = 4.5V, R _G = 1.8Ω
Turn-On Rise Time	t _r	—	24.5	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	66.4	—	ns	
Turn-Off Fall Time	t _f	—	20.8	—	ns	

- Notes:
6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate
 8. Short duration pulse test used to minimize self-heating effect
 9. Guaranteed by design. Not subject to production testing

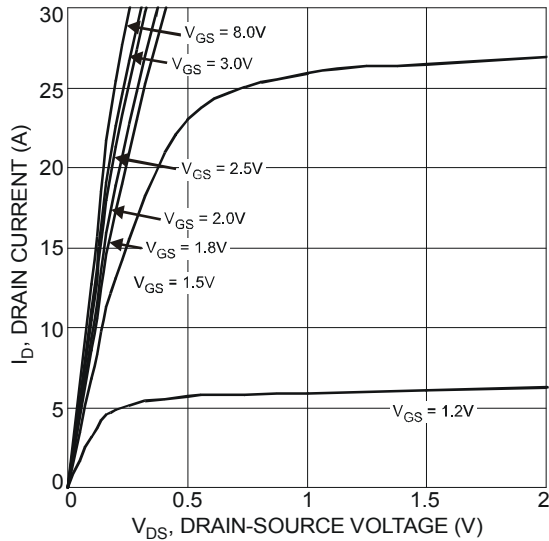


Fig. 1 Typical Output Characteristic

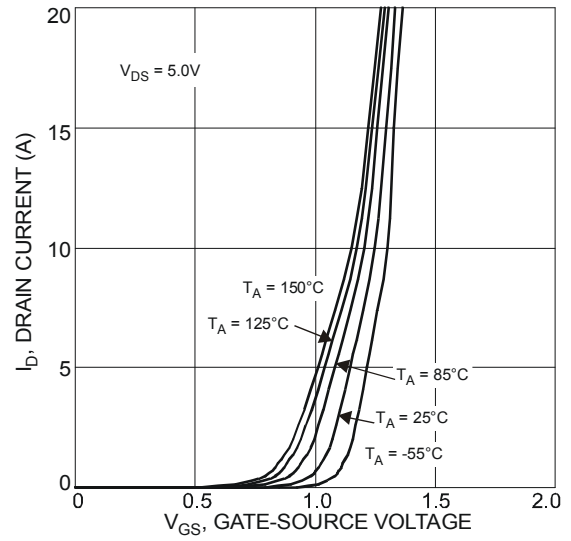


Fig. 2 Typical Transfer Characteristics

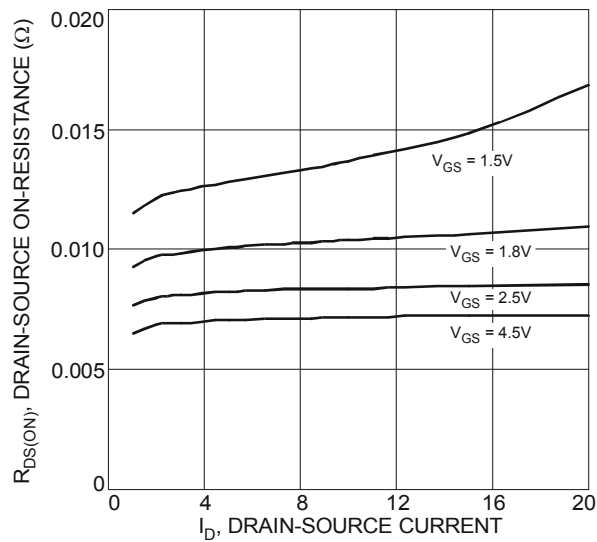


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

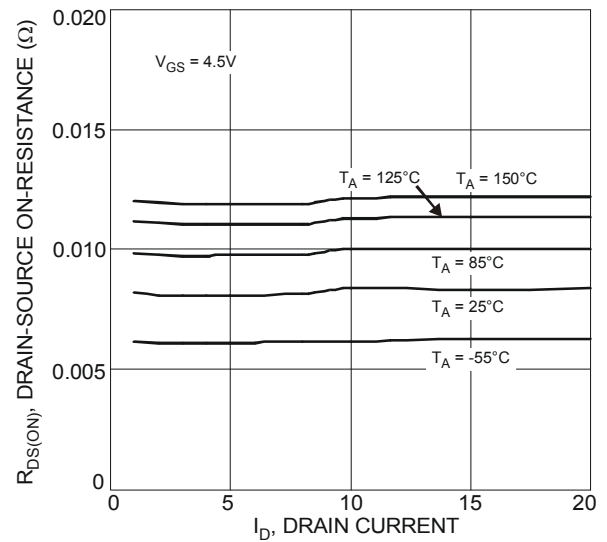


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

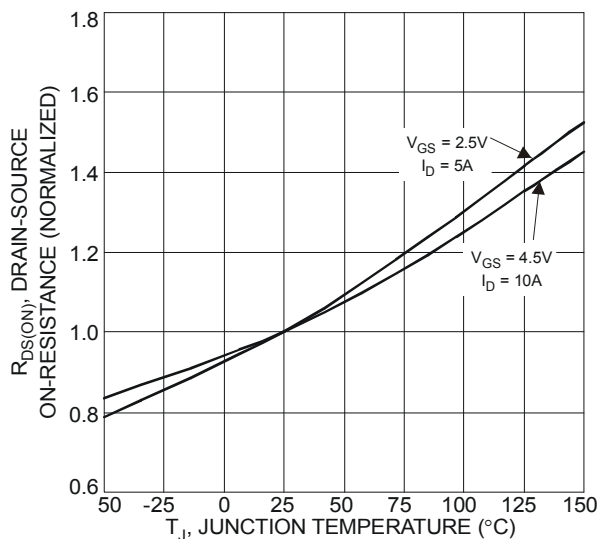


Fig. 5 On-Resistance Variation with Temperature

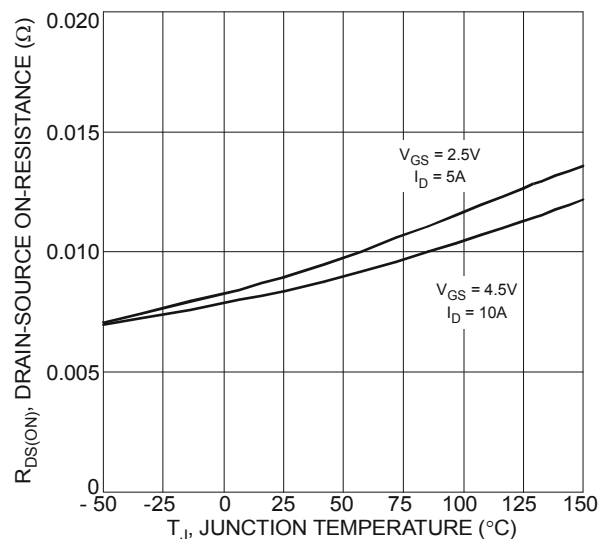


Fig. 6 On-Resistance Variation with Temperature

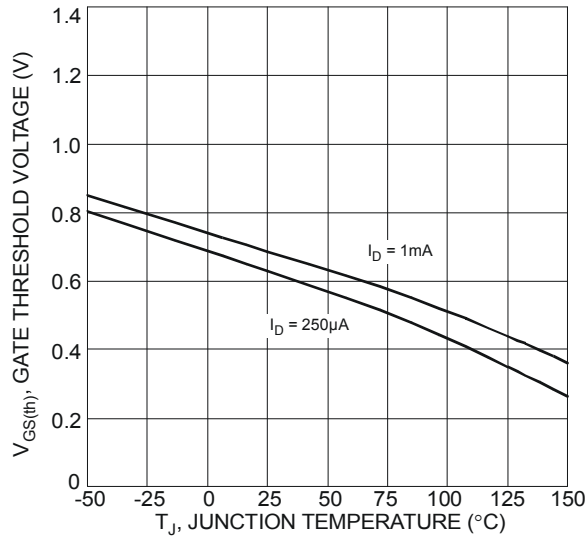


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

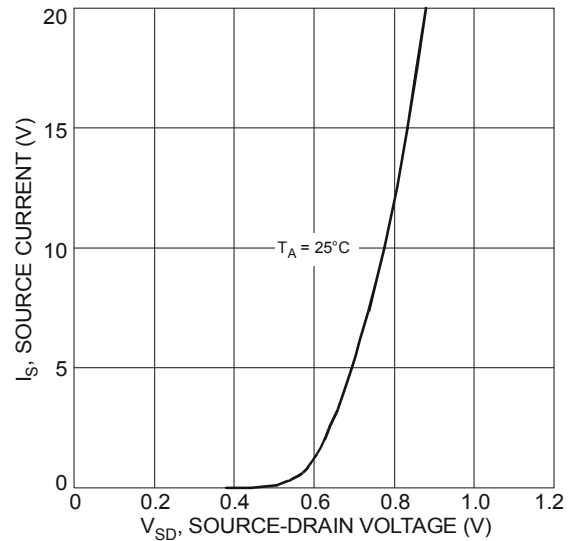


Fig. 8 Diode Forward Voltage vs. Current

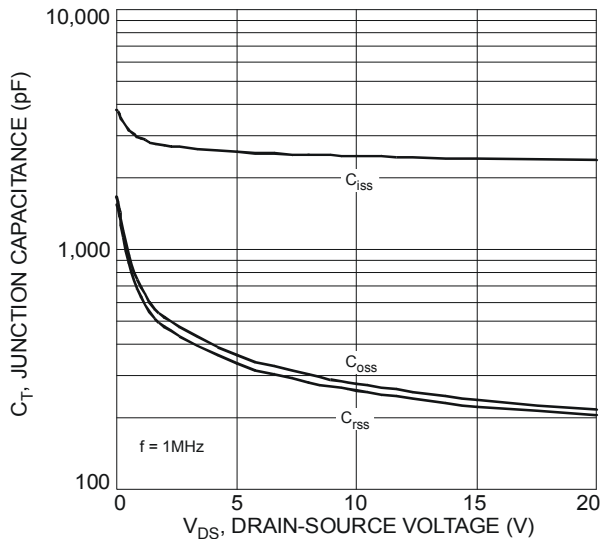


Fig. 9 Typical Junction Capacitance

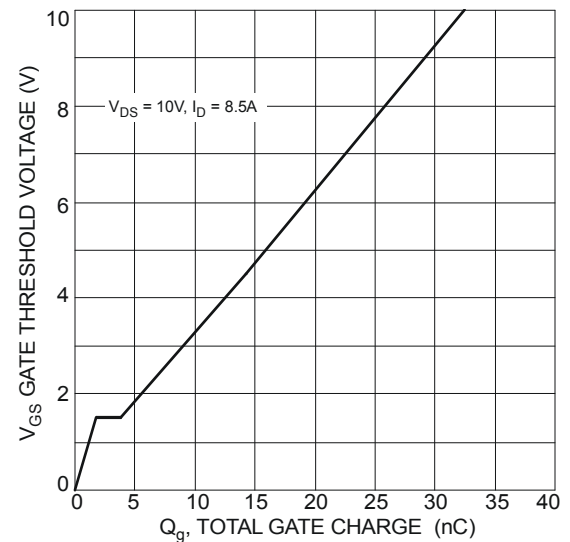


Fig. 10 Gate Charge

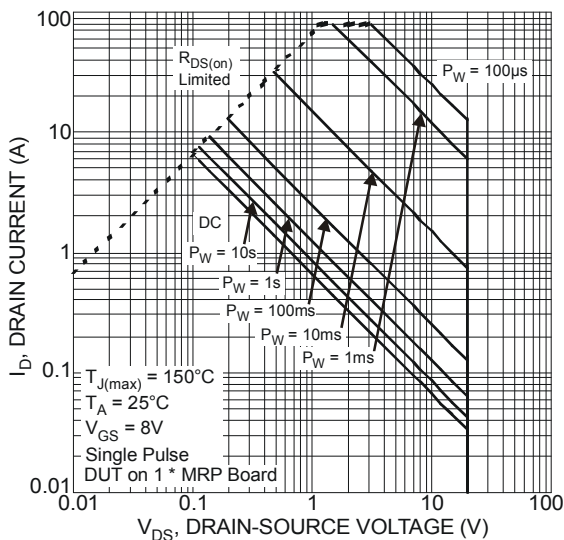
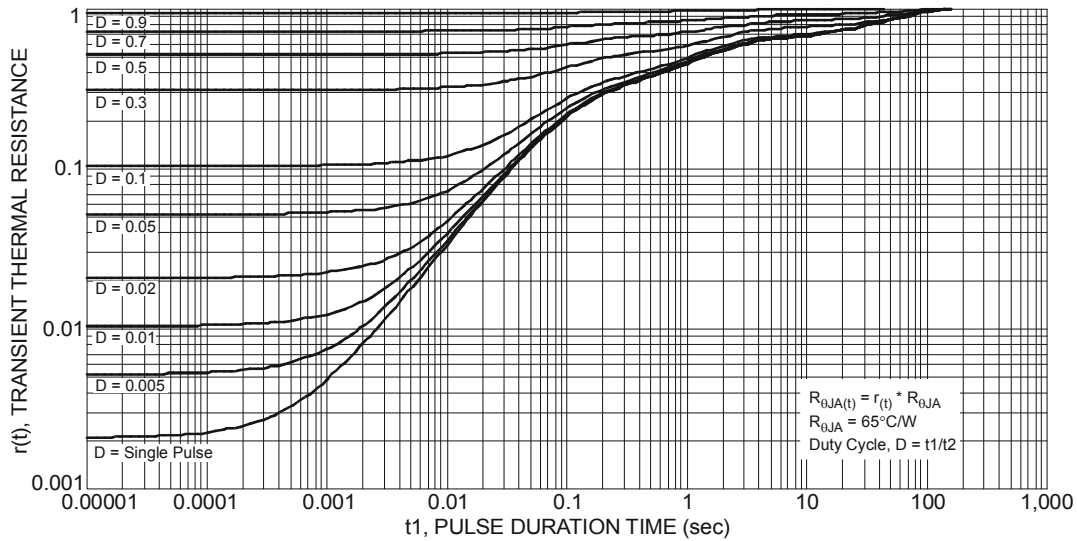
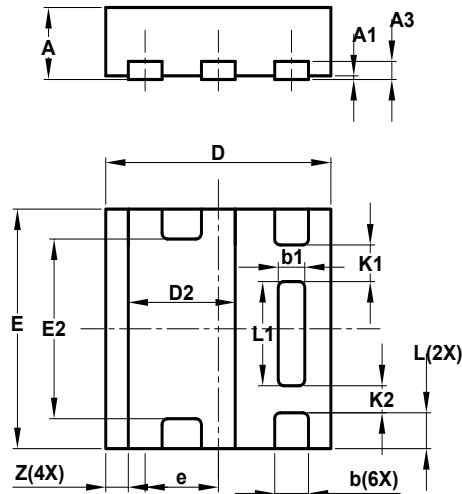


Fig. 11 SOA, Safe Operation Area

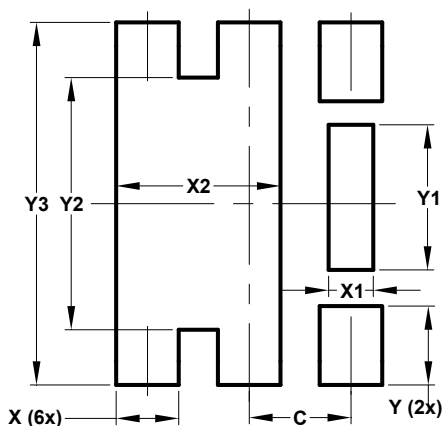


Package Outline Dimensions



U-DFN2020-6 Type E			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	—	—	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	—	—	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	—	—	0.305
K2	—	—	0.225
Z	—	—	0.20
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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